



AOS Semiconductor Product Reliability Report

AO4800B/AO4800BL, rev A

Plastic Encapsulated Device

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This AOS product reliability report summarizes the qualification result for AO4800B. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4800B passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

Table of Contents:

- I. Product Description
- II. Package and Die information
- III. Environmental Stress Test Summary and Result
- IV. Reliability Evaluation
- V. Quality Assurance Information

I. Product Description:

The AO4800B uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in buck converters. Standard Product AO4800B is Pb-free (meets ROHS & Sony 259 specifications).

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	$T_A=25^\circ\text{C}$	6.9	A
	$T_A=70^\circ\text{C}$	5.8	
Pulsed Drain Current	I_{DM}	40	
Power Dissipation	$T_A=25^\circ\text{C}$	1.9	W
	$T_A=70^\circ\text{C}$	1.2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	$T \leq 10\text{s}$	$R_{\theta JA}$	55	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient	Steady-State		90	110	$^\circ\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	40	48	$^\circ\text{C/W}$

II. Die / Package Information:

	AO4800B	AO4800BL (Green Compound)
Process	Standard sub-micron Low voltage N channel process	Standard sub-micron Low voltage N channel process
Package Type	8 leads SOIC	8 leads SOIC
Lead Frame	Copper with Ag spot	Copper with Ag spot
Die Attach	Ag epoxy	Ag epoxy
Bond wire	S: Cu 2mils; G: Au 1.3mils	S: Cu 2mils; G: Au 1.3mils
Mold Material	Epoxy resin with silica filler	Epoxy resin with silica filler
Filler % (Spherical/Flake)	90/10	100/0
Flammability Rating	UL-94 V-0	UL-94 V-0
Backside Metallization	Ti / Ni / Ag	Ti / Ni / Ag
Moisture Level	Up to Level 1 *	Up to Level 1 *

Note * based on info provided by assembler and mold compound supplier

III. Result of Reliability Stress for AO4800B (Standard) & AO4800BL (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
Solder Reflow Precondition	Standard: 1hr PCT+3 cycle reflow@260°C Green: 168hr 85°C /85%RH +3 cycle reflow@260°C	0hr	Standard: 7 lots	770 pcs	0
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 hrs 1000 hrs	1 lot (Note A*)	82 pcs 77+5 pcs / lot	0
HTRB	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 hrs 1000 hrs	1 lot (Note A*)	82 pcs 77+5 pcs / lot	0
HAST	130 +/- 2°C , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 3 lots (Note B**)	165 pcs 50+5 pcs / lot	0
Pressure Pot	121°C , 29.7psi, 100%RH	96 hrs	Standard: 4 lots (Note B**)	220 pcs 50+5 pcs / lot	0
Temperature Cycle	-65°C to 150°C , air to air	250 / 500 cycles	Standard: 7 lots (Note B**)	385 pcs 50+5 pcs / lot	0

III. Result of Reliability Stress for AO4800B (Standard) & AO4800BL (Green) Continues

DPA	Internal Vision Cross-section X-ray	NA	5 5 5	5 5 5	0
CSAM		NA	5	5	0
Bond Integrity	Room Temp 150°C bake 150°C bake	0hr 250hr 500hr	40 40 40	40 wires 40 wires 40 wires	0
Solderability	245°C	5 sec	15	15 leads	0
Die shear	150°C	0hr	10	10	0

Note A: The HTGB and HTRB reliability data presents total of available AO4800B and AO4800BL burn-in data up to the published date.

Note B: The pressure pot, temperature cycle and HAST reliability data for AO4800B and AO4800BL comes from the AOS generic package qualification data.

IV. Reliability Evaluation

FIT rate (per billion):128

MTTF = 891years

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4800B). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.83 \times 10^9 / [2 (164) (168) (258)] = 128$$

$$\text{MTTF} = 10^9 / \text{FIT} = 7.81 \times 10^6 \text{hrs} = 891 \text{years}$$

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from HTRB and HTGB tests

H = Duration of HTRB/HTGB testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] = $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u =The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, 8.617164 X 10⁻⁵eV / K



V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**